

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	34	@ad<"20031002" and (gate adj electrode) same (sidewall adj spacer) same (oxide adj liner)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:29
S1	1	@pn="5899720"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 16:44
S2	140	@ad<"20031002" and gate adj electrode and first adj spacer and second adj spacer and silicide and spacer near3 mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 09:28
S3	10	@ad<"20031002" and gate adj electrode and first adj spacer and second adj spacer and silicide near8 spacer near3 mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 16:54
S4	38	@ad<"20031002" and gate adj electrode and first adj spacer and second adj spacer and silicide same spacer near3 mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 16:55
S5	29	S4 not S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 17:21
S6	220	438/230.ccls. and @ad<"20031002"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 08:51
S7	216	257/E21.626.ccls. and @ad<"20031002"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 09:21

S8	220	438/230.ccls. and @ad<"20031002"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 08:52
S9	200	S7 not S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 08:52
S10	283	257/E21.64.ccls. and @ad<"20031002"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 09:52
S11	272	S10 not S9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 09:21
S12	59	@ad<"20031002" and gate adj electrode and first adj spacer and second adj spacer and silicide and ((etch\$2 chip\$3) near2 substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:06
S13	447	257/900.ccls. and @ad<"20031002"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 09:52
S14	426	S13 not S11	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 13:15
S15	1	@pn="5208472"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 13:15
S16	41	("5208472").URPN.	USPAT	OR	ON	2005/08/02 13:15

S17	785	@ad<"20031002" and gate adj electrode same polysilicon same oxide same tungsten same nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:07
S18	209	@ad<"20031002" and gate adj electrode same polysilicon same (gate adj oxide) same tungsten same (silicon adj nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 15:26